Po-Tsun Liu

List of Publications by Year
in descending order

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295 papers	4,740 citations	101384 36 h-index	168136 53 g-index
298 all docs	298 docs citations	298 times ranked	3162 citing authors

#	Article	IF	Citations
1	Electrical and Photosensitive Characteristics of a-IGZO TFTs Related to Oxygen Vacancy. IEEE Transactions on Electron Devices, 2011, 58, 1121-1126.	1.6	217
2	Environment-dependent metastability of passivation-free indium zinc oxide thin film transistor after gate bias stress. Applied Physics Letters, 2009, 95, .	1.5	201
3	Effects of microwave annealing on electrical enhancement of amorphous oxide semiconductor thin film transistor. Applied Physics Letters, 2012, 101, .	1.5	82
4	The effects of plasma treatment for low dielectric constant hydrogen silsesquioxane (HSQ). Thin Solid Films, 1998, 332, 345-350.	0.8	81
5	Effect of Annealing on Defect Elimination for High Mobility Amorphous Indium-Zinc-Tin-Oxide Thin-Film Transistor. IEEE Electron Device Letters, 2014, 35, 1103-1105.	2.2	79
6	Effects of NH/sub 3/-plasma nitridation on the electrical characterizations of low-k hydrogen silsesquioxane with copper interconnects. IEEE Transactions on Electron Devices, 2000, 47, 1733-1739.	1.6	77
7	Effective repair to ultra-low-k dielectric material (kâˆ¼2.0) by hexamethyldisilazane treatment. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1334.	1.6	77
8	Role of environmental and annealing conditions on the passivation-free in-Gaâ€“Znâ€“O TFT. Thin Solid Films, 2011, 520, 1489-1494.	0.8	74
9	Nitrogenated amorphous InGaZnO thin film transistor. Applied Physics Letters, 2011, 98, .	1.5	74
10	Enhancing the Oxygen Plasma Resistance of Low-kMethylsilsesquioxane by H2Plasma Treatment. Japanese Journal of Applied Physics, 1999, 38, 3482-3486.	0.8	65
11	Effect of oxygen plasma on the surface states of ZnO films used to produce thin-film transistors on soft plastic sheets. Journal of Materials Chemistry C, 2013, 1, 6613.	2.7	65
12	Effects of Microwave Annealing on Nitrogenated Amorphous In-Ga-Zn-O Thin-Film Transistor for Low Thermal Budget Process Application. IEEE Electron Device Letters, 2013, 34, 1157-1159.	2.2	62
13	Multilevel resistive switching memory with amorphous InGaZnO-based thin film. Applied Physics Letters, 2013, 102, .	1.5	62
14	Nickel nanocrystals with HfO2 blocking oxide for nonvolatile memory application. Applied Physics Letters, 2007, 90, 222104.	1.5	61
15	Memory characteristics of Co nanocrystal memory device with HfO2 as blocking oxide. Applied Physics Letters, 2007, 90, 132102.	1.5	57
16	A Novel Nanowire Channel Poly-Si TFT Functioning as Transistor and Nonvolatile SONOS Memory. IEEE Electron Device Letters, 2007, 28, 809-811.	2.2	54
17	The Novel Improvement of Low Dielectric Constant Methylsilsesquioxane by â€‰Nâ€‰2â€‰Oâ€‰ Plasma Treatment. Journal of the Electrochemical Society, 1999, 146, 3802-3806.	1.3	53
18	Effects of H[sub 2] plasma treatment on low dielectric constant methylsilsesquioxane. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 2325.	1.6	50

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19	Metal nanocrystals as charge storage nodes for nonvolatile memory devices. Electrochimica Acta, 2007, 52, 2920-2926.	2.6	50
20	High-performance hydrogenated amorphous-Si TFT for AMLCD and AMOLED applications. IEEE Electron Device Letters, 2005, 26, 731-733.	2.2	48
21	Highly Responsive Blue Light Sensor with Amorphous Indium-Zinc-Oxide Thin-Film Transistor based Architecture. Scientific Reports, 2018, 8, 8153.	1.6	47
22	A Novel Approach of Fabricating Germanium Nanocrystals for Nonvolatile Memory Application. Electrochemical and Solid-State Letters, 2004, 7, G17.	2.2	45
23	Formation of stacked Ni silicide nanocrystals for nonvolatile memory application. Applied Physics Letters, 2007, 90, 112108.	1.5	45
24	Bipolar resistive switching characteristics of Al-doped zinc tin oxide for nonvolatile memory applications. Applied Physics Letters, 2012, 101, 052901.	1.5	45
25	A distributed charge storage with GeO2 nanodots. Applied Physics Letters, 2004, 84, 2581-2583.	1.5	44
26	Charge pumping method for photosensor application by using amorphous indium-zinc oxide thin film transistors. Applied Physics Letters, 2009, 94, 242101.	1.5	44
27	Enhancement of Brightness Uniformity by a New Voltage-Modulated Pixel Design for AMOLED Displays. IEEE Electron Device Letters, 2006, 27, 743-745.	2.2	43
28	Improvement in Integration Issues for Organic Low-k Hybrid-Organic-Siloxane-Polymer. Journal of the Electrochemical Society, 2001, 148, F30.	1.3	42
29	Investigation on amorphous InGaZnO based resistive switching memory with low-power, high-speed, high reliability. Thin Solid Films, 2013, 549, 54-58.	0.8	42
30	Ambient Stability Enhancement of Thin-Film Transistor With InGaZnO Capped With InGaZnO:N Bilayer Stack Channel Layers. IEEE Electron Device Letters, 2011, 32, 1397-1399.	2.2	41
31	Recovering Dielectric Loss of Low Dielectric Constant Organic Siloxane during the Photoresist Removal Process. Journal of the Electrochemical Society, 2002, 149, F81.	1.3	40
32	Design of Bidirectional and Low Power Consumption Gate Driver in Amorphous Silicon Technology for TFT-LCD Application. Journal of Display Technology, 2013, 9, 91-99.	1.3	40
33	Enhancement of reliability and stability for transparent amorphous indium-zinc-tin-oxide thin film transistors. RSC Advances, 2016, 6, 106374-106379.	1.7	40
34	Low-power memory device with NiSi2 nanocrystals embedded in silicon dioxide layer. Applied Physics Letters, 2005, 87, 193504.	1.5	37
35	Electron Charging and Discharging Effects of Tungsten Nanocrystals Embedded in Silicon Dioxide for Low-Voltage Nonvolatile Memory Technology. Electrochemical and Solid-State Letters, 2005, 8, G71.	2.2	37
36	Eliminating dielectric degradation of low-k organosilicate glass by trimethylchlorosilane treatment. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1561.	1.6	36

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37	Low-temperature method for enhancing sputter-deposited HfO2 films with complete oxidization. Applied Physics Letters, 2007, 91, 012109.	1.5	36
38	Electrical switching and transport in the Si/organic monolayer/Au and Si/organic bilayer/Al devices. Applied Physics Letters, 2006, 89, 062105.	1.5	35
39	Using double layer CoSi2 nanocrystals to improve the memory effects of nonvolatile memory devices. Applied Physics Letters, 2007, 90, 212108.	1.5	35
40	Design of Integrated Gate Driver With Threshold Voltage Drop Cancellation in Amorphous Silicon Technology for TFT-LCD Application. Journal of Display Technology, 2011, 7, 657-664.	1.3	35
41	Highly durable and flexible gallium-based oxide conductive-bridging random access memory. Scientific Reports, 2019, 9, 14141.	1.6	35
42	Influence of channel layer and passivation layer on the stability of amorphous InGaZnO thin film transistors. Microelectronics Reliability, 2013, 53, 1879-1885.	0.9	34
43	A New Pixel Circuit Compensating for Brightness Variation in Large Size and High Resolution AMOLED Displays. Journal of Display Technology, 2007, 3, 398-403.	1.3	33
44	High-performance polycrystalline silicon thin-film transistor with multiple nanowire channels and lightly doped drain structure. Applied Physics Letters, 2004, 84, 3822-3824.	1.5	32
45	Improved memory window for Ge nanocrystals embedded in SiON layer. Applied Physics Letters, 2006, 89, 162105.	1.5	30
46	Nonvolatile polycrystalline silicon thin-film-transistor memory with oxide/nitride/oxide stack gate dielectrics and nanowire channels. Applied Physics Letters, 2007, 90, 122111.	1.5	30
47	Solving the integration problem of one transistor one memristor architecture with a Bi-layer IGZO film through synchronous process. Applied Physics Letters, 2018, 112, .	1.5	29
48	Investigation of resistive switching in copper/InGaZnO/Al2O3-based memristor. Applied Physics Letters, 2019, 115, .	1.5	29
49	A promising sputtering route for dense Cu2ZnSnS4 absorber films and their photovoltaic performance. Solar Energy Materials and Solar Cells, 2014, 128, 275-282.	3.0	28
50	Suppression of photo-bias induced instability for amorphous indium tungsten oxide thin film transistors with bi-layer structure. Applied Physics Letters, 2016, 108, 261603.	1.5	28
51	Innovative Voltage Driving Pixel Circuit Using Organic Thin-Film Transistor for AMOLEDs. Journal of Display Technology, 2009, 5, 224-227.	1.3	27
52	Photoresponsivity Enhancement and Extension of the Detection Spectrum for Amorphous Oxide Semiconductor Based Sensors. Advanced Electronic Materials, 2019, 5, 1800824.	2.6	27
53	Short-diode like diffusion capacitance of organic light emission devices. Thin Solid Films, 2006, 498, 244-248.	0.8	26
54	High-gain complementary inverter with InGaZnO/pentacene hybrid ambipolar thin film transistors. Applied Physics Letters, 2010, 97, 083505.	1.5	26

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55	Mobility enhancement for high stability tungsten-doped indium-zinc oxide thin film transistors with a channel passivation layer. RSC Advances, 2018, 8, 6925-6930.	1.7	26
56	TAOS based Cu/TiW/IGZO/Ga2O3/Pt bilayer CBRAM for low-power display technology. Surface and Coatings Technology, 2018, 354, 169-174.	2.2	26
57	Role of tungsten dopants in indium oxide thin-film transistor on radiation hardness technology. Applied Physics Letters, 2020, 116, .	1.5	26
58	Characterization of porous silicate for ultra-low k dielectric application. Thin Solid Films, 2002, 414, 1-6.	0.8	25
59	Effect of bias stress on mechanically strained low temperature polycrystalline silicon thin film transistor on stainless steel substrate. Applied Physics Letters, 2009, 95, .	1.5	25
60	Structural, optical, and photoluminescence study of ZnO/IGZO thin film for thin film transistor application. Materials Letters, 2015, 151, 53-56.	1.3	25
61	Thickness-dependent magnetotransport properties and terahertz response of topological insulator Bi2Te3 thin films. Journal of Alloys and Compounds, 2017, 692, 972-979.	2.8	25
62	Performance Enhancement for Tungsten-Doped Indium Oxide Thin Film Transistor by Hydrogen Peroxide as Cosolvent in Room-Temperature Supercritical Fluid Systems. ACS Applied Materials & Interfaces, 2019, 11, 22521-22530.	4.0	25
63	A low temperature fabrication of HfO2 films with supercritical CO2 fluid treatment. Journal of Applied Physics, 2008, 103, .	1.1	24
64	Bipolar resistive switching characteristics of tungsten-doped indiumâ€“zinc oxide conductive-bridging random access memory. Vacuum, 2019, 166, 226-230.	1.6	24
65	Improvement on Intrinsic Electrical Properties of Low-k Hydrogen Silsesquioxane/Copper Interconnects Employing Deuterium Plasma Treatment. Journal of the Electrochemical Society, 2000, 147, 1186.	1.3	23
66	Enhancing the resistance of low-k hydrogen silsesquioxane (HSQ) to wet stripper damage. Thin Solid Films, 2001, 398-399, 523-526.	0.8	23
67	Investigation of the electrical properties and reliability of amorphous SiCN. Thin Solid Films, 2004, 447-448, 632-637.	0.8	23
68	Effects of Channel Width on Electrical Characteristics of Polysilicon TFTs With Multiple Nanowire Channels. IEEE Transactions on Electron Devices, 2005, 52, 2343-2346.	1.6	23
69	Low-Temperature Passivation of Amorphous-Silicon Thin-Film Transistors With Supercritical Fluids. IEEE Electron Device Letters, 2007, 28, 584-586.	2.2	23
70	Quasisuperlattice storage: A concept of multilevel charge storage. Applied Physics Letters, 2004, 85, 248-250.	1.5	22
71	Characteristic Evolution From Rectifier Schottky Diode to Resistive-Switching Memory With Al-Doped Zinc Tin Oxide Film. IEEE Transactions on Electron Devices, 2014, 61, 1071-1076.	1.6	22
72	Electrical characteristics of InGaZnO thin film transistor prepared by co-sputtering dual InGaZnO and ZnO targets. RSC Advances, 2015, 5, 51983-51989.	1.7	22

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73	Investigation of low operation voltage InZnSnO thin-film transistors with different high-k gate dielectric by physical vapor deposition. Thin Solid Films, 2018, 660, 885-890.	0.8	22
74	Effectively Blocking Copper Diffusion at Low-kHydrogen Silsesquioxane/Copper Interface. Japanese Journal of Applied Physics, 1999, 38, 6247-6252.	0.8	21
75	An interfacial investigation of high-dielectric constant material hafnium oxide on Si substrate. Thin Solid Films, 2005, 488, 167-172.	0.8	21
76	Role of Oxygen in Amorphous In-Ga-Zn-O Thin Film Transistor for Ambient Stability. ECS Journal of Solid State Science and Technology, 2013, 2, Q1-Q5.	0.9	21
77	Improvement of Resistive Switching Uniformity for Alâ€“Znâ€“Snâ€“O-Based Memory Device With Inserting HfO₂ Layer. IEEE Electron Device Letters, 2014, 35, 1233-1235.	2.2	21
78	Effects of Nitrogen on Amorphous Nitrogenated InGaZnO (a-IGZO:N) Thin Film Transistors. Journal of Display Technology, 2016, 12, 1070-1077.	1.3	21
79	Effective Strategy for Porous Organosilicate to Suppress Oxygen Ashing Damage. Electrochemical and Solid-State Letters, 2002, 5, G11.	2.2	20
80	Oxygen Plasma Functioning of Charge Carrier Density in Zinc Oxide Thin-Film Transistors. Applied Physics Express, 2013, 6, 076501.	1.1	20
81	Nonvolatile memory characteristics of nickel-silicon-nitride nanocrystal. Applied Physics Letters, 2007, 91, 082103.	1.5	19
82	Effects of ZnO-nanostructure antireflection coatings on sulfurization-free Cu2ZnSnS4 absorber deposited by single-step co-sputtering process. Applied Physics Letters, 2013, 103, .	1.5	19
83	Trimethylchlorosilane Treatment of Ultralow Dielectric Constant Material after Photoresist Removal Processing. Journal of the Electrochemical Society, 2002, 149, F145.	1.3	18
84	Electrical Transport Phenomena in Aromatic Hydrocarbon Polymer. Journal of the Electrochemical Society, 2003, 150, F7.	1.3	18
85	Modification of intrinsic defects in IZO/IGZO thin films for reliable bilayer thin film transistors. RSC Advances, 2016, 6, 75693-75698.	1.7	18
86	Effect of interfacial layer on device performance of metal oxide thin-film transistor with a multilayer high-k gate stack. Thin Solid Films, 2018, 660, 578-584.	0.8	18
87	High Performance Transparent a-IGZO Thin Film Transistors With ALD-HfO₂ Gate Insulator on Colorless Polyimide Substrate. IEEE Nanotechnology Magazine, 2020, 19, 481-485.	1.1	18
88	The effect of ammonia plasma treatment on low-k methyl-hybrido-silsesquioxane against photoresist stripping damage. Thin Solid Films, 2001, 398-399, 632-636.	0.8	17
89	Polycrystalline silicon thin-film transistor with self-aligned SiGe raised source/drain. Applied Physics Letters, 2002, 81, 4763-4765.	1.5	17
90	Enhanced Performance of Poly-Si Thin Film Transistors Using Fluorine Ions Implantation. Electrochemical and Solid-State Letters, 2005, 8, G246.	2.2	17

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91	A non-selenization technology by co-sputtering deposition for solar cell applications. Optics Letters, 2012, 37, 2760.	1.7	17
92	Effects of Hydrogen on Electrical and Chemical Properties of Low-k Hydrogen Silsesquioxane as an Intermetal Dielectric for Nonetchback Processes. Electrochemical and Solid-State Letters, 1999, 2, 390.	2.2	16
93	Study on the effect of electron beam curing on low-K porous organosilicate glass (OSG) material. Thin Solid Films, 2004, 469-470, 383-387.	0.8	16
94	Improvement of Hydrogenated Amorphous-Silicon TFT Performances With Low-kSiloxane-Based Hydrogen Silsesquioxane (HSQ) Passivation Layer. IEEE Electron Device Letters, 2006, 27, 902-904.	2.2	16
95	Effects of Supercritical Fluids Activation on Carbon Nanotube Field Emitters. IEEE Nanotechnology Magazine, 2007, 6, 29-34.	1.1	16
96	Improvement of Post-Chemical Mechanical Planarization Characteristics on Organic Low k Methylsilsesquioxane as Intermetal Dielectric. Journal of the Electrochemical Society, 2000, 147, 4313.	1.3	15
97	Moisture-Induced Material Instability of Porous Organosilicate Glass. Electrochemical and Solid-State Letters, 2003, 6, F13.	2.2	15
98	Nonvolatile low-temperature polycrystalline silicon thin-film-transistor memory devices with oxide-nitride-oxide stacks. Applied Physics Letters, 2007, 90, 182115.	1.5	15
99	Photoluminescence and Reliability Study of ZnO Cosputtered IGZO Thin-Film Transistors Under Various Ambient Conditions. IEEE Transactions on Electron Devices, 2016, 63, 1578-1581.	1.6	15
100	Mobility enhancement of polycrystalline-Si thin-film transistors using nanowire channels by pattern-dependent metal-induced lateral crystallization. Applied Physics Letters, 2005, 87, 143504.	1.5	14
101	A Novel Self-Aligned Etch-Stopper Structure With Lower Photo Leakage for AMLCD and Sensor Applications. IEEE Electron Device Letters, 2006, 27, 978-980.	2.2	14
102	Application of the low dielectric methyl-silsesquiazane (MSZ) as a passivation layer on TFT-LCD. Thin Solid Films, 2006, 515, 1117-1120.	0.8	14
103	Formation of germanium nanocrystals embedded in silicon-oxygen-nitride layer. Applied Physics Letters, 2006, 89, 052112.	1.5	14
104	Using electroless plating Cu technology for TFT-LCD application. Surface and Coatings Technology, 2010, 205, 1497-1501.	2.2	14
105	Stability study of indium tungsten oxide thin-film transistors annealed under various ambient conditions. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600465.	0.8	14
106	Image reconstruction of a complex cylinder illuminated by TE waves. IEEE Transactions on Microwave Theory and Techniques, 1996, 44, 1921-1927.	2.9	13
107	Structural and Electrical Characteristics of Low-Dielectric Constant Porous Hydrogen Silsesquioxane for Cu Metallization. Journal of the Electrochemical Society, 2003, 150, F141.	1.3	13
108	Improvement of electrical characteristics for fluorine-ion-implanted poly-Si TFTs using ELC. IEEE Electron Device Letters, 2006, 27, 262-264.	2.2	13

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109	Effects of supercritical CO2 fluid on sputter-deposited hafnium oxide. Applied Physics Letters, 2007, 90, 223101.	1.5	13
110	Cuâ•CuMg Gate Electrode for the Application of Hydrogenated Amorphous Silicon Thin-Film Transistors. Electrochemical and Solid-State Letters, 2007, 10, J83.	2.2	13
111	Pi-shape gate polycrystalline silicon thin-film transistor for nonvolatile memory applications. Applied Physics Letters, 2007, 91, .	1.5	13
112	High Endurance and Multilevel Operation in Oxide Semiconductor-Based Resistive RAM Using Thin-Film Transistor as a Selector. ECS Solid State Letters, 2015, 4, Q41-Q43.	1.4	13
113	Electrical performance and stability of tungsten indium zinc oxide thin-film transistors. Materials Letters, 2018, 214, 293-296.	1.3	13
114	Two-Dimensional-Like Amorphous Indium Tungsten Oxide Nano-Sheet Junctionless Transistors with Low Operation Voltage. Scientific Reports, 2019, 9, 7579.	1.6	13
115	Reliability of Multistacked Chemical Vapor Deposited Ti/TiN Structure as the Diffusion Barrier in Ultralarge Scale Integrated Metallization. Journal of the Electrochemical Society, 2000, 147, 368.	1.3	12
116	The novel pattern method of low-k hybrid-organic-siloxane-polymer film using X-ray exposure. Thin Solid Films, 2002, 420-421, 403-407.	0.8	12
117	CMP of ultra low-k material porous-polysilazane (PPSZ) for interconnect applications. Thin Solid Films, 2004, 447-448, 524-530.	0.8	12
118	Effects of Oxygen Plasma Ashing on Barrier Dielectric SiCN Film. Electrochemical and Solid-State Letters, 2005, 8, G11.	2.2	12
119	Effect of deposition temperature and oxygen flow rate on properties of low dielectric constant SiCOH film prepared by plasma enhanced chemical vapor deposition using diethoxymethylsilane. Surface and Coatings Technology, 2006, 200, 3134-3139.	2.2	12
120	Dielectric Hafnium Oxide Improved by Supercritical Carbon Dioxide Fluid Treatment for Pentacene Thin-Film Transistors. Electrochemical and Solid-State Letters, 2008, 11, H165.	2.2	12
121	The influence on electrical characteristics of amorphous indium tungsten oxide thin film transistors with multi-stacked active layer structure. Thin Solid Films, 2018, 666, 94-99.	0.8	12
122	Performance improvements of tungsten and zinc doped indium oxide thin film transistor by fluorine based double plasma treatment with a high-K gate dielectric. Thin Solid Films, 2018, 665, 117-122.	0.8	12
123	Annealing effects on resistive switching of IGZO-based CBRAM devices. Vacuum, 2020, 180, 109630.	1.6	12
124	Effect of Annealing Treatment on Performance of Ga2O3 Conductive-Bridging Random-Access Memory. Journal of Electronic Materials, 2020, 49, 6817-6822.	1.0	12
125	Dielectric characteristics of low-permittivity silicate using electron beam direct patterning for intermetal dielectric applications. Applied Physics Letters, 2003, 83, 4226-4228.	1.5	11
126	Cu-penetration induced breakdown mechanism for a-SiCN. Thin Solid Films, 2004, 469-470, 388-392.	0.8	11

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127	Effects of Channel Width and NH[sub 3] Plasma Passivation on Electrical Characteristics of Polysilicon Thin-Film Transistors by Pattern-Dependent Metal-Induced Lateral Crystallization. Journal of the Electrochemical Society, 2005, 152, G545.	1.3	11
128	High-performance metal-induced lateral-crystallization polysilicon thin-film transistors with multiple nanowire channels and multiple gates. IEEE Nanotechnology Magazine, 2006, 5, 157-162.	1.1	11
129	Nonvolatile Siâˆ•SiO2âˆ•SiNâˆ•SiO2âˆ•Si type polycrystalline silicon thin-film-transistor memory with nanowire channels for improvement of erasing characteristics. Applied Physics Letters, 2007, 91, 193103.	1.5	11
130	Investigation of the low dielectric siloxane-based hydrogen silsesquioxane (HSQ) as passivation layer on TFT-LCD. Thin Solid Films, 2007, 516, 374-377.	0.8	11
131	Application of Supercritical CO[sub 2] Fluid for Dielectric Improvement of SiO[sub x] Film. Electrochemical and Solid-State Letters, 2009, 12, H35.	2.2	11
132	Design of Analog Pixel Memory for Low Power Application in TFT-LCDs. Journal of Display Technology, 2011, 7, 62-69.	1.3	11
133	Electrical Performance Enhancement of Alâ€“Zn-Snâ€“O Thin Film Transistor by Supercritical Fluid Treatment. IEEE Electron Device Letters, 2013, 34, 1154-1156.	2.2	11
134	Photovoltaic electrical properties of aqueous grown ZnO antireflective nanostructure on Cu(In,Ga)Se_2 thin film solar cells. Optics Express, 2014, 22, A13.	1.7	11
135	Polystyrene-block-poly(methylmethacrylate) composite material film as a gate dielectric for plastic thin-film transistor applications. RSC Advances, 2014, 4, 18493-18502.	1.7	11
136	Enhancement of Barrier Properties in Chemical Vapor Deposited TiN Employing Multi-Stacked Ti/TiN Structure. Japanese Journal of Applied Physics, 2000, 39, L82-L85.	0.8	10
137	Reliability of laser-activated low-temperature polycrystalline silicon thin-film transistors. Applied Physics Letters, 2002, 80, 4780-4782.	1.5	10
138	Electrical Enhancement of Solid Phase Crystallized Poly-Si Thin-Film Transistors with Fluorine Ion Implantation. Journal of the Electrochemical Society, 2006, 153, G815.	1.3	10
139	The Instability of a-Si:H TFT under Mechanical Strain with High Frequency ac Bias Stress. Electrochemical and Solid-State Letters, 2007, 10, J113.	2.2	10
140	Application of secondary electron potential contrast on junction leakage isolation. Applied Physics Letters, 2009, 95, 122105.	1.5	10
141	Silicon induced stability and mobility of indium zinc oxide based bilayer thin film transistors. Applied Physics Letters, 2016, 109, .	1.5	10
142	The Influence of Annealing Temperature on Amorphous Indiumâ€Zincâ€Tungsten Oxide Thinâ€Film Transistors. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700785.	0.8	10
143	Enhanced Electrical Characteristics of Ge nMOSFET by Supercritical Fluid CO₂ Treatment With H₂O₂Cosolvent. IEEE Electron Device Letters, 2021, 42, 645-648.	2.2	10
144	Electrical properties of metalâ€“ferroelectricâ€“insulatorâ€“semiconductor using solâ€“gel derived SrBi2Ta2O9 film and ultra-thin Si3N4 buffer layer. Thin Solid Films, 2002, 420-421, 377-381.	0.8	9

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145	Preventing dielectric damage of low-k organic siloxane by passivation treatment. Microelectronic Engineering, 2002, 60, 469-475.	1.1	9
146	Study on SONOS Nonvolatile Memory Technology Using High-Density Plasma CVD Silicon Nitride. Electrochemical and Solid-State Letters, 2004, 7, G113.	2.2	9
147	Reduction of leakage current in metal-induced lateral crystallization polysilicon TFTs with dual-gate and multiple nanowire channels. IEEE Electron Device Letters, 2005, 26, 646-648.	2.2	9
148	Integration issues for siloxane-based hydrogen silsesquioxane (HSQ) applied on TFT-LCDs. Thin Solid Films, 2006, 498, 70-74.	0.8	9
149	Suppression of Schottky leakage current in island-in amorphous silicon thin film transistors with the Cuâ•CuMg as source/drain metal. Applied Physics Letters, 2007, 91, 062103.	1.5	9
150	Low temperature improvement on silicon oxide grown by electron-gun evaporation for resistance memory applications. Applied Physics Letters, 2008, 93, 052903.	1.5	9
151	Enhanced stability of thin film transistors with double-stacked amorphous IWO/IWO:N channel layer. Semiconductor Science and Technology, 2018, 33, 065001.	1.0	9
152	Elimination of Dielectric Degradation for Chemical-Mechanical Planarization of Low-kHydrogen Silisesquioxane. Japanese Journal of Applied Physics, 2001, 40, 3143-3146.	0.8	8
153	A study of parasitic resistance effects in thin-channel polycrystalline silicon TFTs with tungsten-clad source/drain. IEEE Electron Device Letters, 2003, 24, 509-511.	2.2	8
154	CMP of Low-k Methylsilsesquiazane with Oxygen Plasma Treatment for Multilevel Interconnect Applications. Electrochemical and Solid-State Letters, 2004, 7, G122.	2.2	8
155	Fabrication of NiSi2 nanocrystals embedded in SiO2 with memory effect by oxidation of the amorphous Siâ•Niâ•SiO2 structure. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 851-855.	0.9	8
156	Activation of Carbon Nanotube Emitters by Using Supercritical Carbon Dioxide Fluids with Propyl Alcohol. Electrochemical and Solid-State Letters, 2006, 9, G124.	2.2	8
157	Nickel silicide nanocrystals embedded in SiO2 and HfO2 for nonvolatile memory application. Thin Solid Films, 2007, 516, 360-363.	0.8	8
158	Formation of cobalt-silicide nanocrystals in Ge-doped dielectric layer for the application on nonvolatile memory. Applied Physics Letters, 2008, 92, 152115.	1.5	8
159	Effect of high-pressure H₂O treatment on elimination of interfacial GeO_X layer between ZrO₂ and Ge stack. Applied Physics Letters, 2011, 99, 082907.	1.5	8
160	P-8: Low Power Gate Driver Circuits for Narrow Bezel Panel Application. Digest of Technical Papers SID International Symposium, 2012, 43, 1076-1078.	0.1	8
161	Efficiency enhancement of non-selenized Cu(In,Ga)Se2 solar cells employing scalable low-cost antireflective coating. Nanoscale Research Letters, 2014, 9, 331.	3.1	8
162	Electromagnetic transverse electric-wave inverse scattering of a conductor by the genetic algorithm. International Journal of Imaging Systems and Technology, 1998, 9, 388-394.	2.7	7

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163	High performance and high reliability polysilicon thin-filmiyansistors with multiple nano-wire channels. , 0, , .		7
164	Temperature Effects of n-MOSFET Devices with Uniaxial Mechanical Strains. Electrochemical and Solid-State Letters, 2006, 9, G276.	2.2	7
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